



Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from,Europe,America and south Asia,supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of “Quality Parts,Customers Priority,Honest Operation,and Considerate Service”,our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip,ALPS,ROHM,Xilinx,Pulse,ON,Everlight and Freescale. Main products comprise IC,Modules,Potentiometer,IC Socket,Relay,Connector.Our parts cover such applications as commercial,industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



Contact us

Tel: +86-755-8981 8866 Fax: +86-755-8427 6832

Email & Skype: info@chipsmall.com Web: www.chipsmall.com

Address: A1208, Overseas Decoration Building, #122 Zhenhua RD., Futian, Shenzhen, China



SOT23 PNP SILICON PLANAR MEDIUM POWER TRANSISTOR

FM M T555

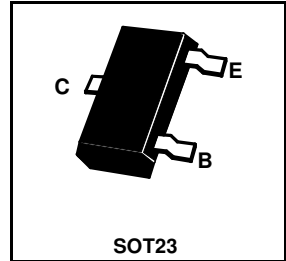
ISSUE 4 – AUGUST 2003

FEATURES

- * 150 Volt V_{CEO}
- * 1 Amp continuous current

COMPLEMENTARY TYPE – FM M T455

PARTMARKING DETAIL – 555



ABSOLUTE MAXIMUM RATINGS.

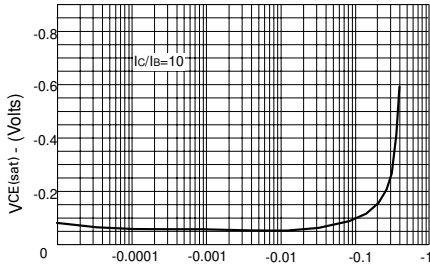
PARAMETER	SYMBOL	VALUE	UNIT
Collector-Base Voltage	V_{CBO}	-160	V
Collector-Emitter Voltage	V_{CEO}	-150	V
Emitter-Base Voltage	V_{EBO}	-5	V
Peak Pulse Current	I_{CM}	-2	A
Continuous Collector Current	I_C	-1	A
Base Current	I_B	-200	mA
Power Dissipation at $T_{amb} = 25^\circ\text{C}$	P_{tot}	500	mW
Operating and Storage Temperature Range	T_j, T_{stg}	-55 to +150	$^\circ\text{C}$

ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^\circ\text{C}$ unless otherwise stated).

PARAMETER	SYMBOL	MIN.	MAX.	UNIT	CONDITIONS.
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	-160		V	$I_C = -10\mu\text{A}$
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	-150		V	$I_C = -10\text{mA}^*$
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	-5		V	$I_E = -10\mu\text{A}$
Collector Cut-Off Current	I_{CBO}		-0.1 -10	μA A	$V_{CB} = -140\text{V}$ $V_{CB} = -140\text{V}, T_{amb} = 100^\circ\text{C}$
Emitter Cut-Off Current	I_{EBO}		-0.1	μA	$V_{EB} = -4\text{V}$
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$		-0.3	V	$I_C = -100\text{mA}, I_B = -10\text{mA}^*$
Base-Emitter Saturation Voltage	$V_{BE(sat)}$		-1	V	$I_C = -100\text{mA}, I_B = -10\text{mA}^*$
Base-Emitter Turn-on Voltage	$V_{BE(on)}$		-1	V	$I_C = -100\text{mA}, V_{CE} = -10\text{V}^*$
Static Forward Current Transfer Ratio	h_{FE}	50 50	300		$I_C = -10\text{mA}, V_{CE} = -10\text{V}^*$ $I_C = -300\text{mA}, V_{CE} = -10\text{V}^*$
Transition Frequency	f_T	100		MHz	$I_C = -50\text{mA}, V_{CE} = -10\text{V}$ $f = 100\text{MHz}$
Output Capacitance	C_{obo}		10	pF	$V_{CB} = -10\text{V}, f = 1\text{MHz}$

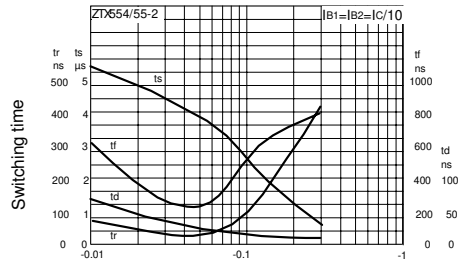
* Measured under pulsed conditions. Pulse width = $300\mu\text{s}$. Duty cycle $> 2\%$
Spice parameter data is available upon request for this device

TYPICAL CHARACTERISTICS



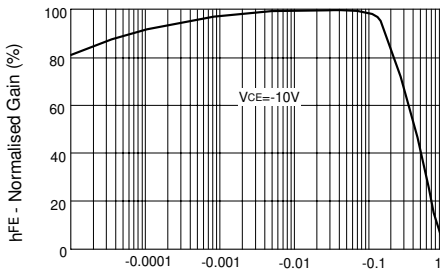
IC - Collector Current (Amps)

VCE(sat) v IC



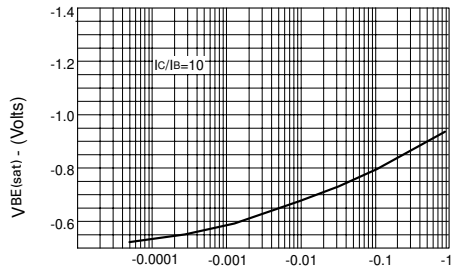
IC - Collector Current (Amps)

Switching Speeds



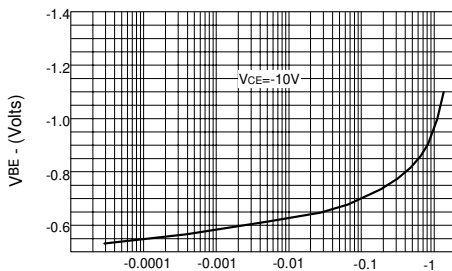
IC - Collector Current (Amps)

hFE v IC



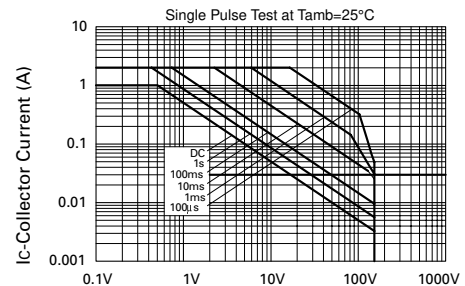
IC - Collector Current (Amps)

VBE(sat) v IC



IC - Collector Current (Amps)

VBE(on) v IC



VCE - Collector Emitter Voltage (V)

Safe Operating Area